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RESPONSE UNDER 37 C.F.R. §1.116
RECEIVED EXPEDITED PROCEDURE
GROUP ART UNIT: 2811

NOV -8 2000

IR-1677 (2-1984)

TC 2800 MAIL ROOM

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Zhijun QU et al.

Serial No.: 09/329,156

Filed: June 9, 1999

For: **DUAL EPITAXIAL LAYER FOR HIGH VOLTAGE VERTICAL CONDUCTION POWER MOSFET DEVICES**

Date: November 3, 2000

Group Art Unit: 2811

Examiner: S. Hu

Assistant Commissioner for Patents

Box AF

Washington, D.C. 20231

AMENDMENT TRANSMITTAL LETTER - FEE COMPUTATION

Transmitted herewith is an amendment in the above-identified application.

___ "Small Entity" status (37 C.F.R. §1.9 & §1.27) established
___ previously ___ by enclosed verified statement.

OFGS Check No. ___, which includes the fee of \$ -0- calculated below, is attached.

NO. CLAIMS AFTER AMENDMENT			HIGHEST NO. PREVIOUSLY PAID FOR			EXTRA PRESENT		RATE	ADDIT. FEE
TOTAL	12	MINUS	20	* =	0	X		(\$9 SE or \$18)	\$ -0-
INDEP.	2	MINUS	3	** =	0	X		(\$40 SE or \$80)	\$ -0-
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM						X		(\$135 SE or \$270)	\$ -0-
* not less than 20			** not less than 3			TOTAL \$ -0-			

In the event the actual fee is greater than the payment submitted or is inadvertently not enclosed or if any additional fee during the prosecution of this application is not paid, the Patent Office is authorized to charge the underpayment to Deposit Account No. 15-0700.

If this communication is filed after the shortened statutory time period had elapsed and no separate Petition is enclosed, the Commissioner of Patents and Trademarks is petitioned, under 37 C.F.R. §1.136(a), to extend the time for filing a response to the outstanding Office Action by the number of months which will avoid abandonment under 37 C.F.R. §1.135. The fee under 37 C.F.R. § 1.17 should be charged to our Deposit Account No. 15-0700.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231, on November 3, 2000:

Mark D. Torché

Name of applicant, assignee or
Registered Representative

Signature

November 3, 2000

Date of Signature

MDT:ck
00478878.1

Respectfully submitted,

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EXPEDITED PROCEDURE
GROUP ART UNIT: 2811

IR-1677 (2-1984)

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In re Patent Application of:

Zhijun QU et al.

Serial No.: 09/329,156

Filed: June 9, 1999

For: DUAL EPITAXIAL LAYER FOR HIGH VOLTAGE VERTICAL CONDUCTION
POWER MOSFET DEVICES

New York, New York

Date: November 3, 2000

Group Art Unit: 2811

Examiner: S. Hu

Assistant Commissioner for Patents
Box AF
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. 1.116

Sir:

In response to the Office Action mailed August 3, 2000, please reconsider the
above-identified application amended as follows:

IN THE CLAIMS:

Please amend claims 1 and 10 as follows:

1. (Twice Amended) A semiconductor device comprising, in combination, a
silicon substrate having a first and second surface; a first layer disposed on [of epitaxial silicon
formed atop] said first surface and having impurities of the n or p conductivity type uniformly
distributed throughout the volume of said first layer; a second layer disposed on [of epitaxial
silicon formed atop the surface of] said first layer; said second layer [and coextensive therewith]